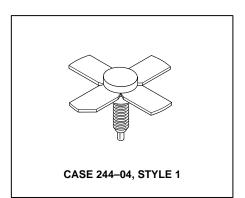
The RF Line NPN Silicon RF Power Transistor

 \dots designed for 12.5 volt VHF large—signal power amplifiers in commercial and industrial FM equipment.

- Compact .280 Stud Package
- Specified 12.5 V, 175 MHz Performance Output Power = 15 Watts Power Gain = 12 dB Min Efficiency = 60% Min
- Characterized to 220 MHz
- · Load Mismatch Capability at High Line and Overdrive

MRF2628

15 W 136-220 MHz RF POWER TRANSISTOR NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	18	Vdc
Collector–Base Voltage	V _{СВО}	36	Vdc
Emitter–Base Voltage	V _{EBO}	4.0	Vdc
Collector Current — Continuous	IC	2.5	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	40 0.23	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Junction Temperature	TJ	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.0	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

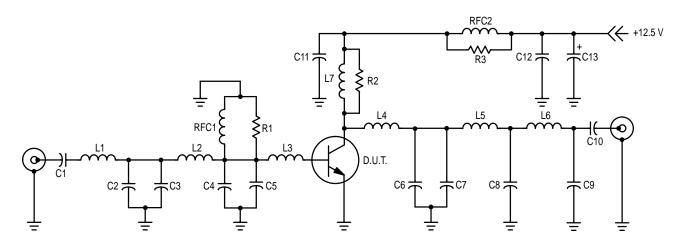
, •	•				
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 25 mAdc, I _B = 0)	V(BR)CEO	18	_	_	Vdc
Collector–Emitter Breakdown Voltage (I _C = 25 mAdc, V _{BE} = 0)	V(BR)CES	36	_	_	Vdc
Emitter–Base Breakdown Voltage (I _E = 5.0 mAdc, I _C = 0)	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (V _{CB} = 15 Vdc, I _E = 0)	ICBO	_	_	1.0	mAdc

(continued)



ELECTRICAL CHARACTERISTICS — **continued** $(T_C = 25^{\circ}C)$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS					
DC Current Gain (IC = 500 mAdc, VCE = 5.0 Vdc)	hFE	10	70	150	_
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 15 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	33	60	pF
FUNCTIONAL TESTS (Figure 1)					
Common–Emitter Amplifier Power Gain (V _{CC} = 12.5 Vdc, P _{Out} = 15 W, f = 175 MHz)	G _{pe}	12	13	_	dB
Collector Efficiency (V _{CC} = 12.5 Vdc, P _{out} = 15 W, f = 175 MHz)	η	60	68	_	%
Load Mismatch (V _{CC} = 15.5 Vdc, P _{in} = 2.0 dB Overdrive, Load VSWR = 30:1)	Ψ	No Degradation in Output Power			



C1, C10, C11 — 1000 pF Ceramic Chip Capacitor

C2 — 27 pF Mini Unelco Capacitor

C3 — 33 pF Mini Unelco Capacitor

C4, C5 — 270 pF Unelco J101 Capacitor C6, C9 — 18 pF Mini Unelco Capacitor

C7 — 91 pF Mini Unelco Capacitor

C8 — 68 pF Mini Unelco Capacitor

C12 — 0.1 µF Monolythic Capacitor

C13 — 100 μ F, 15 V Electrolytic L1 — 3 Turns #18 AWG, 3/16" ID

L2 — 1-1/8" #18 AWG into 1/2" High Loop

L3 — Copper Pad, 0.200 x 0.400 x 0.060

L4 — 1/4" #18 AWG into 1/8" High Loop

L5 — 3 Turns #24 AWG Enameled, 3/32" ID

L6 — 6 Turns #24 AWG Enameled, 3/32" ID

L7 — 1-3/4" #16 AWG into 3/4" High Loop

R1 — 12 Ω , 1/2 W Carbon

 $R2 - 100 \Omega$, 1.0 W Carbon

R3 — 10 Ω , 1.0 W Carbon

RFC1 — $0.15\,\mu H$ Molded Choke

RFC2 — Ferroxcube Choke, VK200-4B

Figure 1. Broadband Circuit

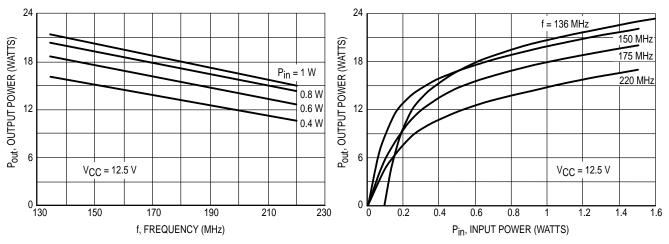


Figure 2. Output Power versus Frequency

Figure 3. Output Power versus Input Power

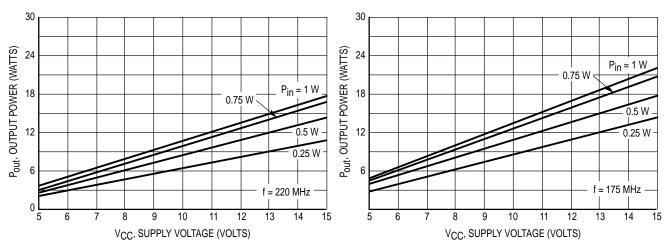


Figure 4. Output Power versus Supply Voltage

Figure 5. Output Power versus Supply Voltage

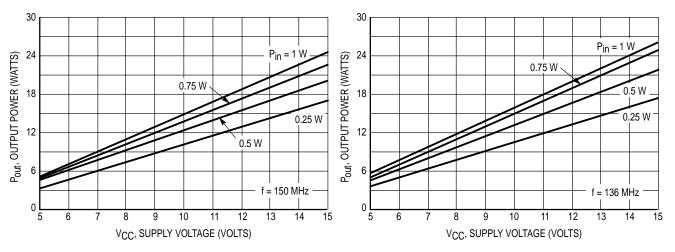


Figure 6. Output Power versus Supply Voltage

Figure 7. Output Power versus Supply Voltage

MOTOROLA RF DEVICE DATA MRF2628

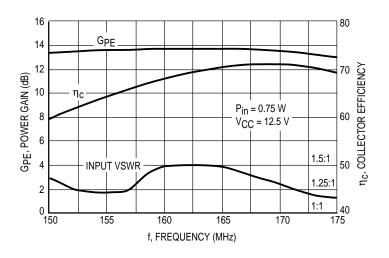
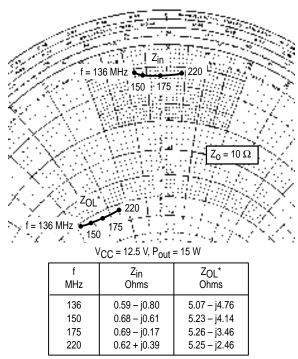


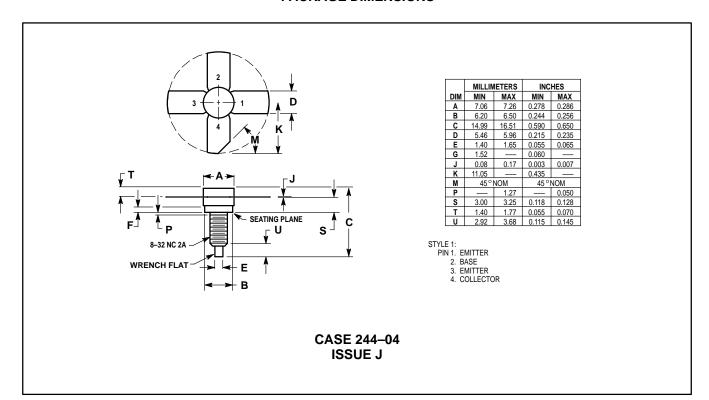
Figure 8. Typical Performance in a Broadband Circuit



Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 9. Series Equivalent Impedance

PACKAGE DIMENSIONS



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